Abstracts

Monolithic GaAs Dual-Gate FET Variable Power Amplifier Module

P. Saunier, H.Q. Tserng, B. Kim and G.H. Westphal. "Monolithic GaAs Dual-Gate FET Variable Power Amplifier Module." 1985 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 85.1 (1985 [MCS]): 1-3.

The design, fabrication, and microwave performance of a monolithic four-stage GaAs dual-gate FET amplifier are described. A linear gain of 23 dB with 250 mW output power has been measured at 18 GHz. The highest power obtained was 500 mW with 21 dB gain at the same frequency. By varying the second gate bias voltage, a dynamic gain control range of more than 60 dB has been observed. The chip size is 6.45mm x 2.1mm x 0.1mm.

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